



Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638
 Phone: (562) 404-4474 * Fax: (562) 404-1773
 ssdi@ssdi-power.com * www.ssdi-power.com

DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

SFF340

Screening ^{2/}

___ = Not Screened

TX = TX Level

TXV = TXV Level

S = S Level

Package

/66= TO-66

SFF340/66

**10 AMP
 N-CHANNEL
 POWER MOSFET
 400 Volts
 0.55 Ω**

Features:

- Rugged Construction with Poly Silicon Gate
- Low $R_{DS(ON)}$ and High Transconductance
- Excellent High Temperature Stability
- Very Fast Switching Speed
- Fast Recovery and Superior dV/dt Performance
- Increased Reverse Energy Capability
- Low Input and Transfer Capacitance for Easy Paralleling
- Hermetically Sealed Package
- TX, TXV, and S-Level Screening Available ^{2/}
- Replacement for IRF340 Types

Maximum Ratings ^{3/}	Symbol	Value	Unit
Drain – Source Voltage	V_{DS}	400	V
Gate – Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_{D1} I_{D2}	10 7.2	A
		@ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	
Avalanche Energy (Single Pulse)	E_{AS}	5.7	mJ
Avalanche Current	I_{AR}	10	A
Power Dissipation	P_D	63 48	W
		@ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	
Operating & Storage Temperature	Top & Tstg	-55 to +150	$^\circ\text{C}$
Thermal Resistance (Junction to Case)	$R_{\theta JC}$	2	$^\circ\text{C/W}$

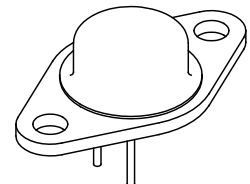
NOTES: *Pulsed per MIL-STD-750.

^{1/} For ordering information, price, and availability - contact factory.

^{2/} Screening based on MIL-PRF-19500. Screening flows available on request.

^{3/} Unless otherwise specified, all electrical characteristics @ 25°C .

TO-66



NOTE: All specifications are subject to change without notification.
 SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00317C

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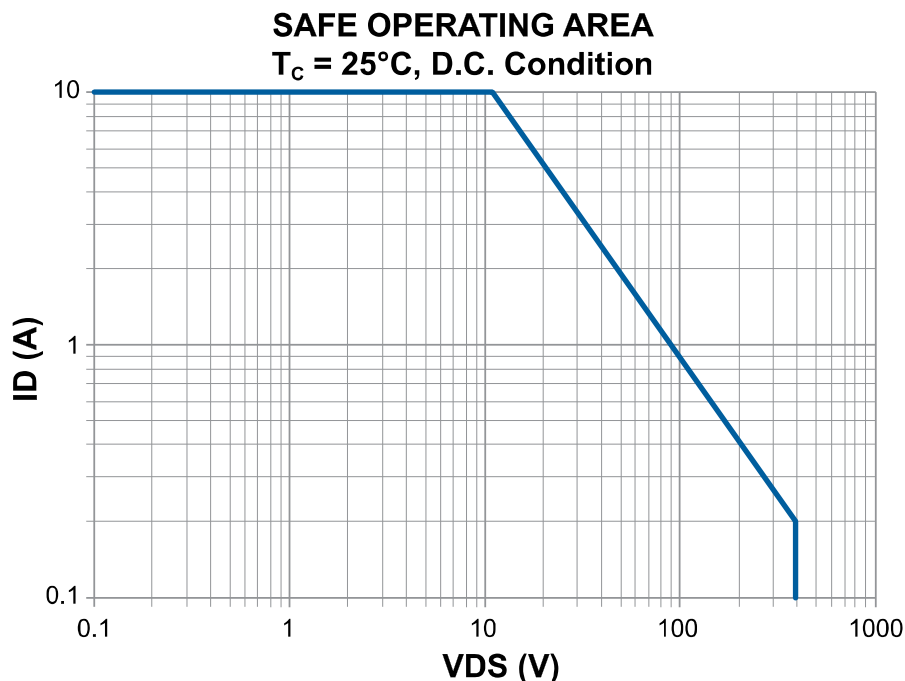


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SFF340/66

Electrical Characteristics ^{3/}		Symbol	Min	Typ	Max	Unit
Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	400	450	—	V
Drain to Source On State Resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$	$R_{DS(on)}$	—	0.5	0.55	Ω
On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10\text{ V}$	$I_{D(on)}$	10	—	—	A
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2.0	3.2	4.0	V
Forward Transconductance	$V_{DS} \geq 50\text{ V}, I_{DS} = 6\text{ A}$	g_{fs}	5	6	—	S(V)
Zero Gate Voltage Drain Current	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_A = 125^\circ\text{C}$	I_{DSS}	—	0.1 1.0	25 250	μA
Gate to Source Leakage Forward	At rated V_{GS}	I_{GSS}	—	1	+100	nA
Gate to Source Leakage Reverse			—	1	-100	
Total Gate Charge	$V_{GS} = 10\text{ V}$	Q_g	—	25	50	nC
Gate to Source Charge	80% rated V_{DS}	Q_{gs}	—	6	10	
Gate to Drain Charge	$I_D = 10\text{ A}$	Q_{gd}	—	12	25	
Turn on Delay Time	$V_{DD} = 200\text{ V}$ $I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$	$t_{d(on)}$	—	28	40	nsec
Rise Time		t_r	—	27	60	
Turn off Delay Time		$t_{d(off)}$	—	75	100	
Fall Time		t_f	—	15	30	
Diode Forward Voltage	$I_S = 10\text{ A}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	V_{SD}	—	—	2.0	V
Diode Reverse Recovery Time	$T_J = 25^\circ\text{C}, I_F = 10\text{ A},$ $di/dt = 100\text{ A}/\mu\text{sec}$	t_{rr}	170	600	700	nsec
Reverse Recovery Charge		Q_{RR}	1.6	6.7	8	μC
Input Capacitance	$V_{GS} = 0\text{ V}$	C_{iss}	—	3500	—	pF
Output Capacitance	$V_{DS} = 25\text{ V}$	C_{oss}	—	340	—	
Reverse Transfer Capacitance	$f = 1\text{ MHz}$	C_{rss}	—	90	—	



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SFF340/66

PACKAGE OUTLINE: TO-213AA (TO-66)

PIN 1 (CASE): DRAIN

PIN 2: SOURCE

PIN 3: GATE

DIM	MIN	MAX
A	0.250	0.340
ØB	0.028	0.034
ØD ^{1/}	—	0.620
ØD1	0.470	0.500
E	0.190	0.210
E1	0.093	0.107
F ^{2/}	0.050	0.075
F1 ^{1/}	—	0.050
L	0.360	—
ØP	0.142	0.161
Q	0.950	0.970
R1	—	0.350
R2	—	0.145
S	0.570	0.590

NOTES:

^{1/} The outline contour is optional within zone defined by ØD and F1.

^{2/} Dimension does NOT include sealing flanges.

